

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~striketrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims 1-8 and add new claims 9-10 in accordance with the following:

1. (CURRENTLY AMENDED) A semiconductor device substrate comprised of a core substrate having, on both main surfaces of which, respective interconnect patterns are ~~formed via~~ extending through resin layers, wherein:

the core substrate ~~is formed by~~ being of a material having a heat expansion coefficient closer to that of a semiconductor chip than the respective heat expansion coefficients of the main resin layers and the interconnect patterns ~~inside the substrate,~~ and

a resin layer, forming an outermost layer of the semiconductor device substrate on each of the main surfaces thereof, of a material having at least one of a higher strength and a higher elongation than a resin material used for inner resin layers ~~in of the semiconductor device~~ substrate and preventing cracking~~[[.]]~~ and deformation, ~~and other problems arising in of the semiconductor device~~ substrate due to thermal stress occurring between two or more of the core substrate, ~~and~~ the inner resin layers, and the interconnect patterns in the semiconductor device substrate.

2. (CURRENTLY AMENDED) The semiconductor device substrate as set forth in claim 1, wherein a further resin layer, under the resin layer forming the outermost layer of the semiconductor device substrate, is made of a resin material having at least one of a higher strength and a higher elongation than the resin material of the inner resin layers in the semiconductor device substrate.

3. (CURRENTLY AMENDED) The semiconductor device substrate as set forth in claim 1, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and an elongation of at least 10%.

4. (CURRENTLY AMENDED) The semiconductor device substrate as set forth in claim 2, wherein ~~the~~ resin material forming the outermost layer has a fracture strength of at least

90 MPa and an elongation of at least 10%.

5. (CURRENTLY AMENDED) A semiconductor device substrate, comprising:
a core substrate having, on both main surfaces of which, respective interconnect patterns ~~are formed~~ extending through via resin layers[[:]],
the [[a]] core substrate being of a material having a heat expansion coefficient closer to that of a semiconductor chip than the respective heat expansion coefficients of resin layers and interconnect patterns inside the semiconductor device substrate; and
a resin layer, of a material having a-at least one of a higher strength and a higher elongation than a resin material used for the resin layers inside the semiconductor device substrate, forming an outermost layer on each of the opposite main surfaces of the semiconductor device substrate.

6. (CURRENTLY AMENDED) The semiconductor device substrate as set forth in claim 5, wherein a further resin layer, under the resin layer forming the outermost layer of the semiconductor device substrate, is made of a resin material having at least one of a higher strength and a higher elongation than the resin material of the inner resin layers in the semiconductor device substrate.

7. (CURRENTLY AMENDED) The semiconductor device substrate as set forth in claim 5, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and an elongation of at least 10%.

8. (CURRENTLY AMENDED) The semiconductor device substrate as set forth in claim 6, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and an elongation of at least 10%.

9. (NEW) A substrate for a chip, comprising:
a first resin layer forming an outermost layer on each of opposite main surfaces of the substrate;
a second resin layer underlying the first resin layer;
a third resin layer underlying the second resin layer; and
a core underlying the third resin layer having, on both main surfaces, respective interconnect patterns between the core and at least one of the first resin layer, the second resin

layer, and the third resin layer,

wherein at least one of the first resin layer and the second resin layer being of a material having at least one of a higher strength and a higher elongation than a material used for the third resin layer.

10. (NEW) The substrate according to claim 9, wherein material forming the first resin layer has a fracture strength of at least 90 MPa and an elongation of at least 10%.